Supporting Information

Facile fabrication of hierarchical N-doped GaZn mixed oxides for water splitting reaction

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Fig. S1 X-ray mapping of N-GaZn mixed oxide (glycine as N-precursor) activated at 500 °C.
**Fig. S2** Current voltage curves for N-GaZn mixed oxide (glycine as N-precursor) electrodes under (A) UV irradiation (> 300 nm) (B) visible irradiation (> 420 nm) in 0.1 M Na$_2$SO$_4$ (pH 5.9).

Fig S2 (A) depicts the current-voltage curves of N-doped GaZn mixed oxide electrodes under UV irradiation. Anodic photocurrent was clearly observed the electrode and exhibited highest photocurrent of 0.016 mA/cm$^2$ at 0.95 V vs. Ag/AgCl. The presence of anodic photocurrent indicates that the photocatalysts are n-type semiconductors.
Fig. S3 Water splitting reaction without sacrificial agent over N-doped GaZn mixed oxide using glycine as precursor.

Fig. S4 Reusability study over N-doped GaZn mixed oxide using glycine as precursor.